

AMENDMENTS TO THE CLAIMS

Please amend the Claims as follows. Insertions are shown underlined while deletions are ~~struck through~~. Please add claims 8-24.

1 (original): A polishing pad having a polishing region and a light-transmitting region used in chemical mechanical polishing, wherein the light-transmitting region satisfies that the difference  $\Delta T$  ( $\Delta T = T_0 - T_1$ ) (%) between  $T_0$  and  $T_1$  is within 10 (%) over the whole range of measurement wavelengths of from 400 to 700 nm, wherein  $T_1$  is the light transmittance (%) of the light-transmitting region measured at the measurement wavelength  $\lambda$  after dipping in a KOH aqueous solution at pH 11 for 24 hours and  $T_0$  is the light-transmittance (%) measured at the measurement wavelength  $\lambda$  before the dipping.

2 (original): A polishing pad having a polishing region and a light-transmitting region used in chemical mechanical polishing, wherein the light-transmitting region satisfies that the difference  $\Delta T$  ( $\Delta T = T_0 - T_1$ ) (%) between  $T_0$  and  $T_1$  is within 10 (%) over the whole range of measurement wavelengths of from 400 to 700 nm, wherein  $T_1$  is the light transmittance (%) of the light-transmitting region measured at the measurement wavelength  $\lambda$  after dipping in an  $H_2O_2$  aqueous solution at pH 4 for 24 hours and  $T_0$  is the light-transmittance (%) measured at the measurement wavelength  $\lambda$  before the dipping.

3 (currently amended): The polishing pad according to claim 1 ~~or 2~~, wherein the material forming the light-transmitting region is non-foam.

4 (currently amended): The polishing pad according to ~~any of claims 1 to 3~~ claim 1, wherein the material forming the polishing region is fine-cell foam.

5 (currently amended): The polishing pad according to ~~any of claims 1 to 4~~ claim 1, wherein the light-transmitting region at the polishing side does not have an uneven structure retaining and renewing an abrasive liquid.

6 (currently amended): The polishing pad according to ~~any of claims 1 to 5~~ claim 1, wherein the polishing region at the polishing side is provided with grooves.

7 (currently amended): A method of manufacturing a semiconductor device, which comprises a step of polishing the surface of a semiconductor wafer with the polishing pad according to ~~any of claims 1 to 6~~ claim 1.

8 (new): The polishing pad according to claim 2, wherein the material forming the light-transmitting region is non-foam.

9 (new): The polishing pad according to 2, wherein the material forming the polishing region is fine-cell foam.

10 (new): The polishing pad according to 3, wherein the material forming the polishing region is fine-cell foam.

11 (new): The polishing pad according to claim 2, wherein the light-transmitting region at the polishing side does not have an uneven structure retaining and renewing an abrasive liquid.

12 (new): The polishing pad according to claim 3, wherein the light-transmitting region at the polishing side does not have an uneven structure retaining and renewing an abrasive liquid.

13 (new): The polishing pad according to claim 4, wherein the light-transmitting region at the polishing side does not have an uneven structure retaining and renewing an abrasive liquid.

14 (new): The polishing pad according to claim 2, wherein the polishing region at the polishing side is provided with grooves.

15 (new): The polishing pad according to claim 3, wherein the polishing region at the polishing side is provided with grooves.

16 (new): The polishing pad according to claim 4, wherein the polishing region at the polishing side is provided with grooves.

17 (new): The polishing pad according to claim 5, wherein the polishing region at the polishing side is provided with grooves.

18 (new): A method of manufacturing a semiconductor device, which comprises a step of polishing the surface of a semiconductor wafer with the polishing pad according to claim 2.

19 (new): A polishing pad for chemical mechanical polishing comprising:

a polishing region having a through-hole in an axial direction; and

a light-transmitting region fitted in the through-hole, said light-transmitting region being constituted by a material satisfying that  $\Delta T$  which is a difference between  $T_0$  (%) and  $T_1$  (%) is within 10 percentage points as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein  $T_1$  is a light transmittance (%) measured at a measurement wavelength  $\lambda$  after dipping the material for 24 hours in a KOH aqueous solution having a pH of 11 or in an  $H_2O_2$  aqueous solution having pH of 4,

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and  $T_0$  is a light-transmittance (%) measured at the measurement wavelength  $\lambda$  before the dipping.

20 (new): The polishing pad according to claim 19, wherein the material forming the light-transmitting region is non-foam.

21 (new): The polishing pad according to claim 19, further comprising a cushion layer laminated on a back side of the polishing region opposite to its polishing side, wherein the cushion layer has a through-hole at the same position as the light-transmitting region with respect to the axial direction.

22 (new): The polishing pad according to claim 21, wherein the cushion layer is laminated on the polishing region using a double-coated tape.

23 (new): The polishing pad according to claim 19, wherein the material is a polyurethane resin comprising an organic isocyanate, a polyol, and a chain extender.

24 (new): The polishing pad according to claim 23, wherein in the polyurethane resin, a ratio of the number of isocyanate groups of the organic isocyanate to the number of functional groups of the polyol and the chain extender in total is 0.95 to 1.15.